

FIG. 1

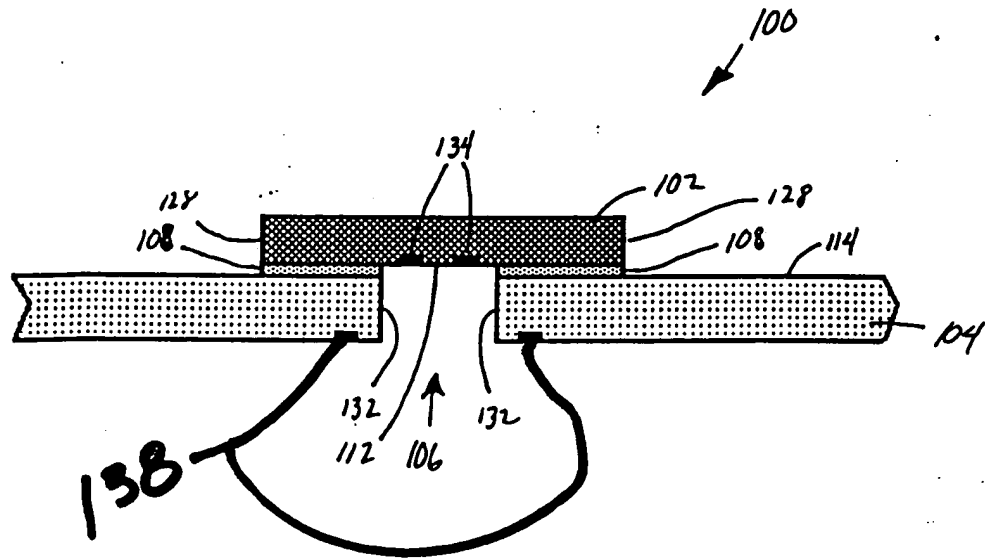
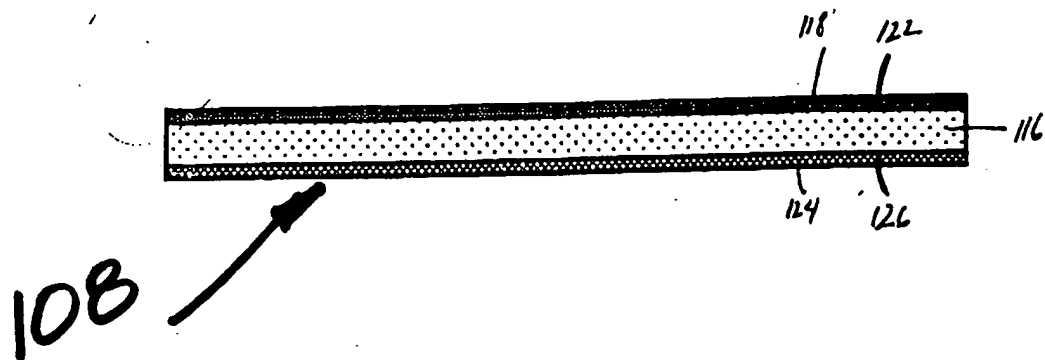


FIG. 2



005040" 40001560

On the 11th of March 1944, the following was received from the Ministry of War:

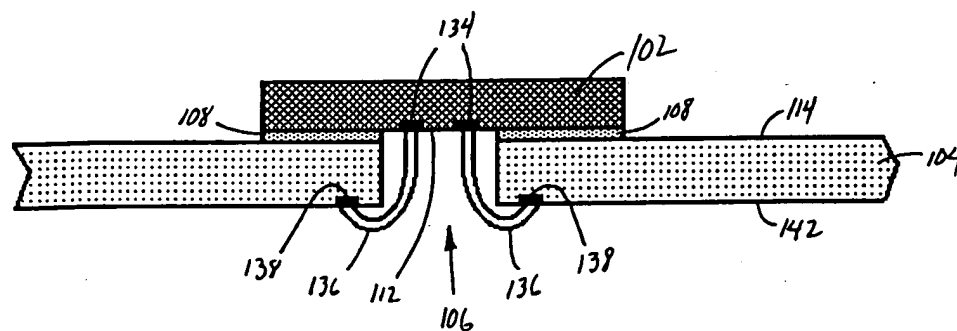


FIG. 4

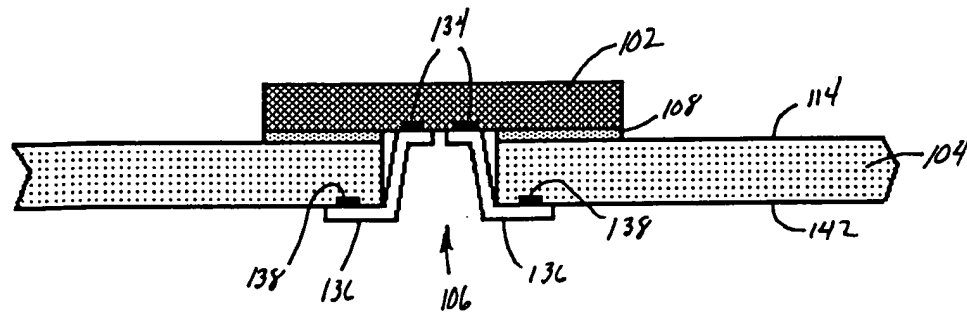


FIG. 5

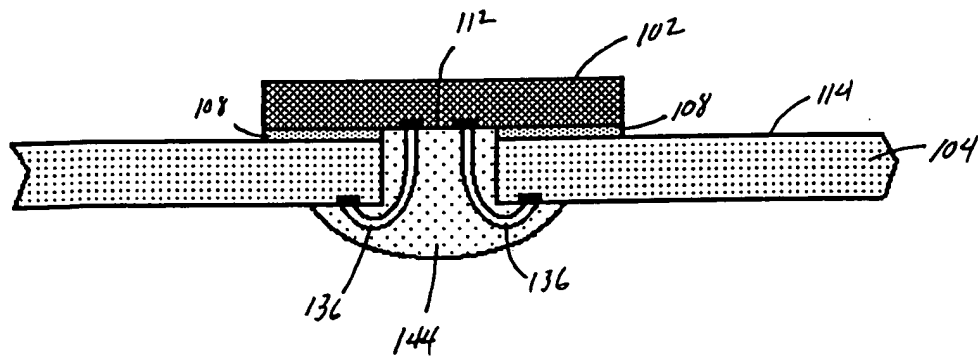


FIG. 6

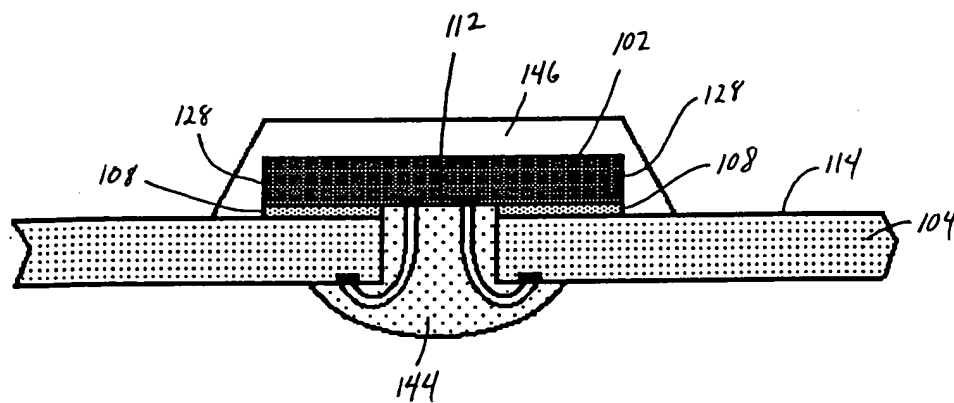


FIG. 7

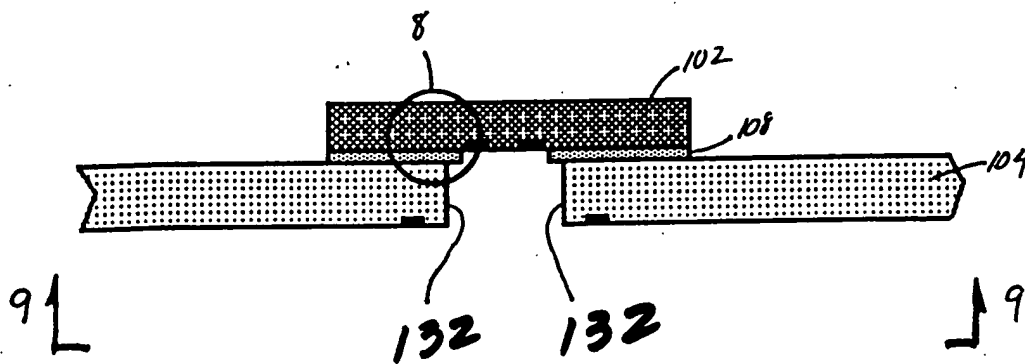


FIG. 8

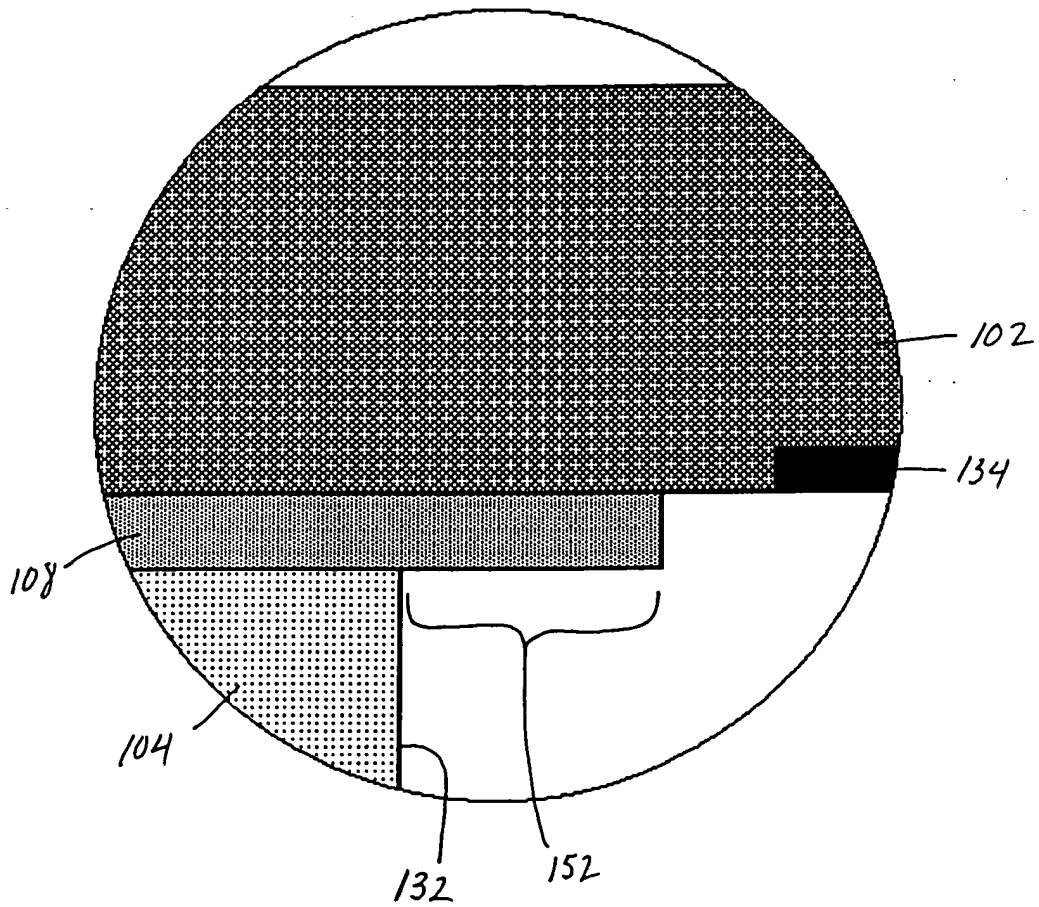
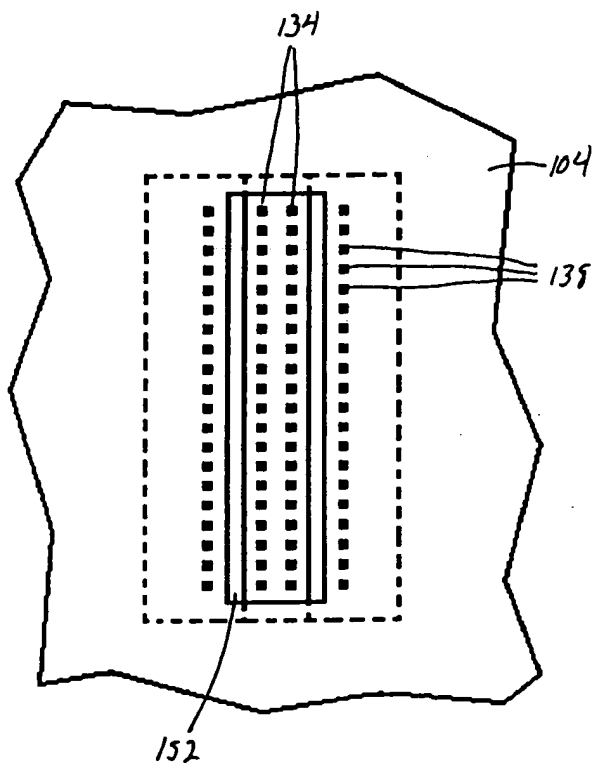




FIG. 9



005070" 1E0E1500

FIG. 10

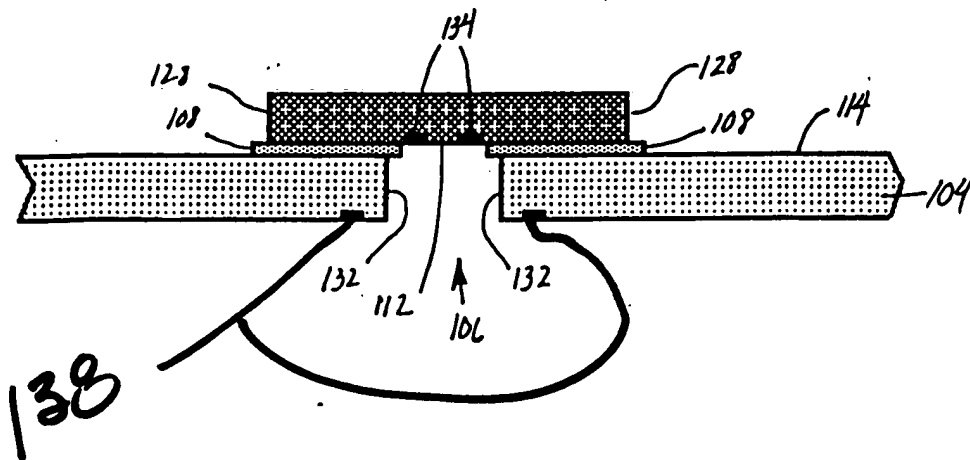


FIG. 11

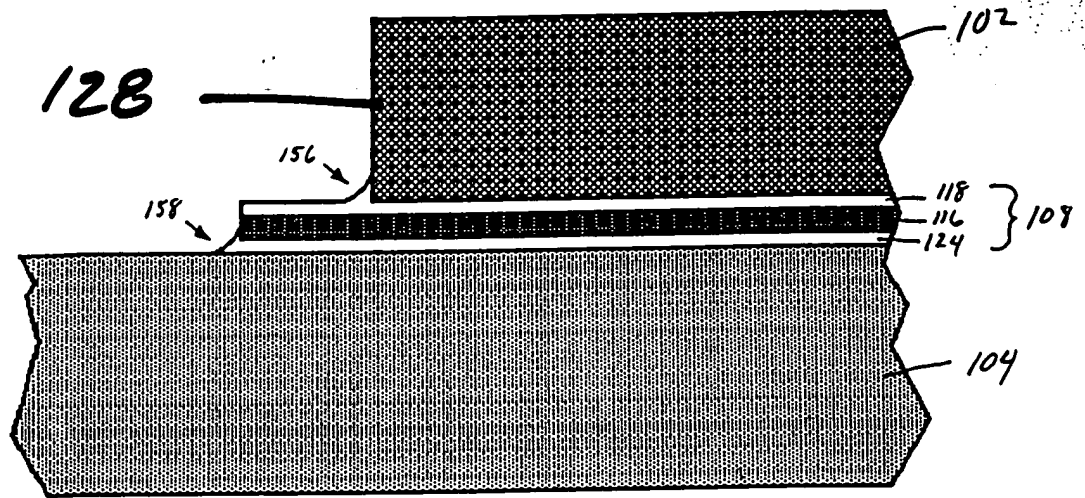


FIG. 12

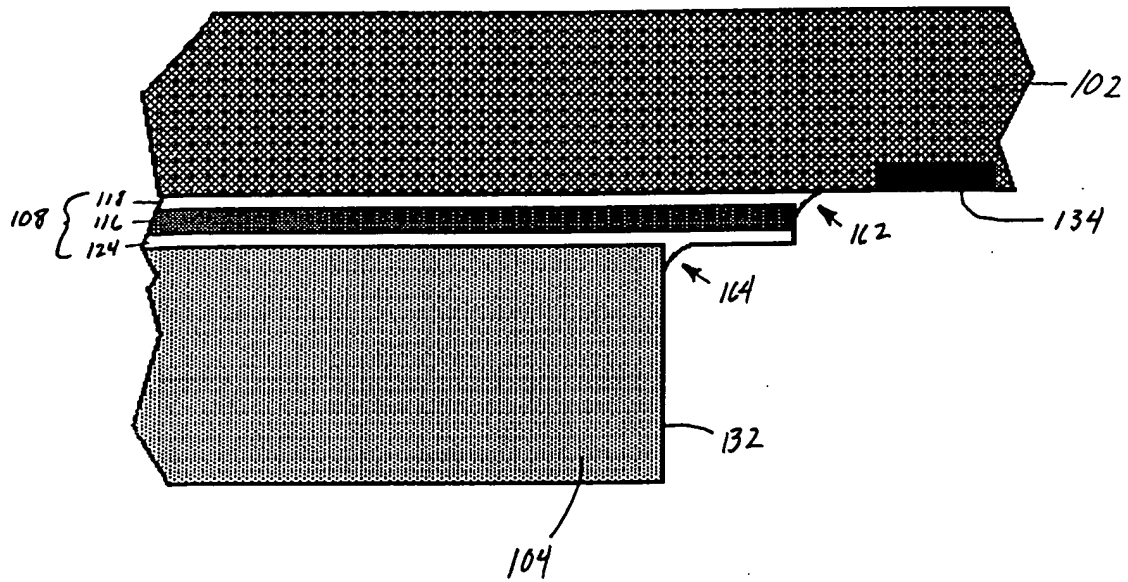
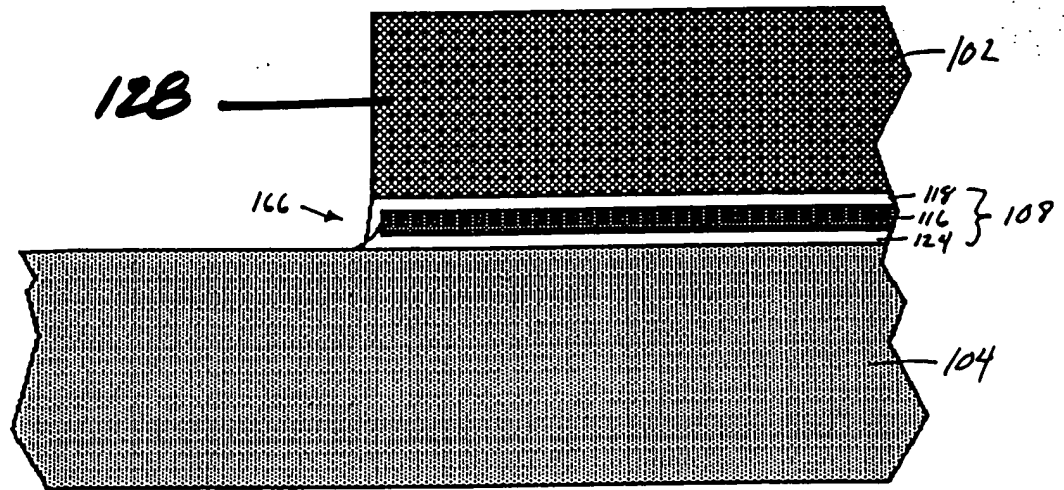
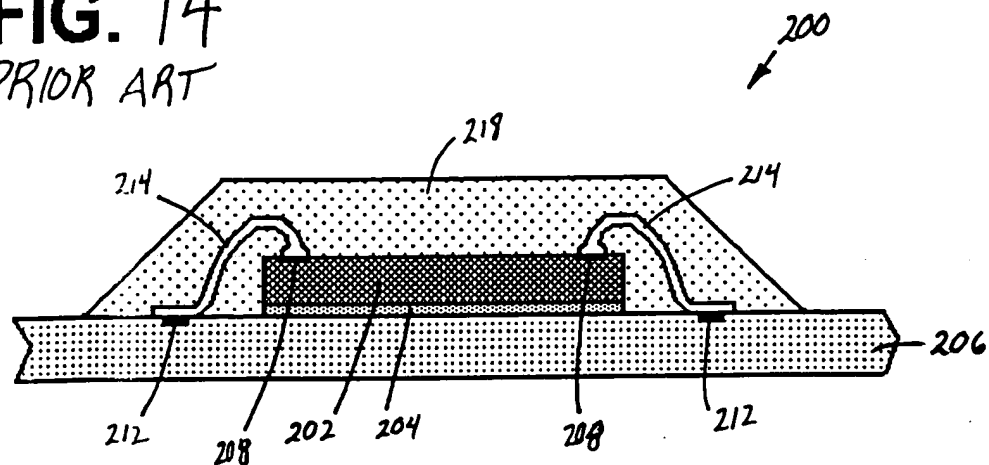


FIG. 13

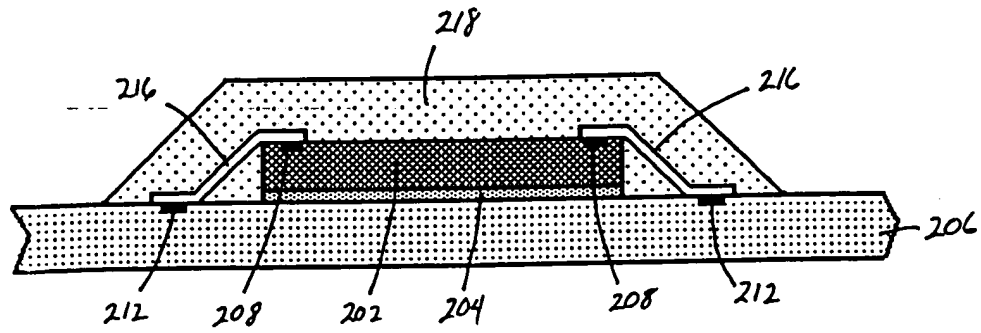


**FIG. 14**  
PRIOR ART



005070" 16021560

**FIG. 15**  
PRIOR ART



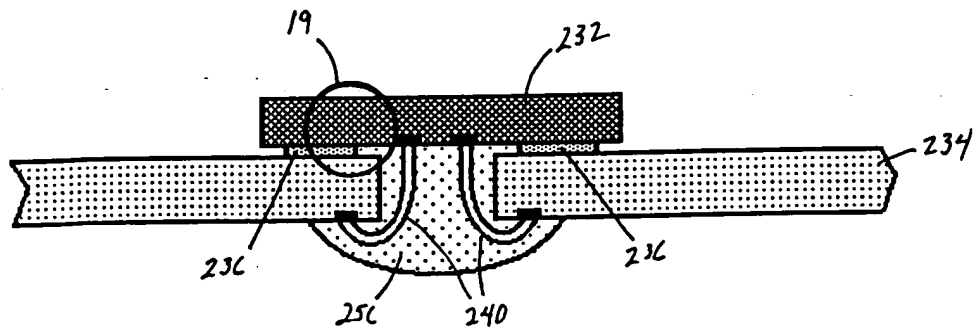
005070" 1E0E+560

This diagram shows a cross-sectional view of a semiconductor device. A central channel region (262) is defined by a gate stack (242) on top of a substrate (232). The gate stack includes a gate dielectric (246) and a gate electrode (248). The channel region is flanked by side gate regions (236) which are part of a larger substrate (250). The side gates are connected to a common terminal (234). The device is shown with various layers and regions labeled with reference numerals: 232, 234, 236, 240, 242, 244, 246, 248, 250, 252, 254, 258, 262, and 264.

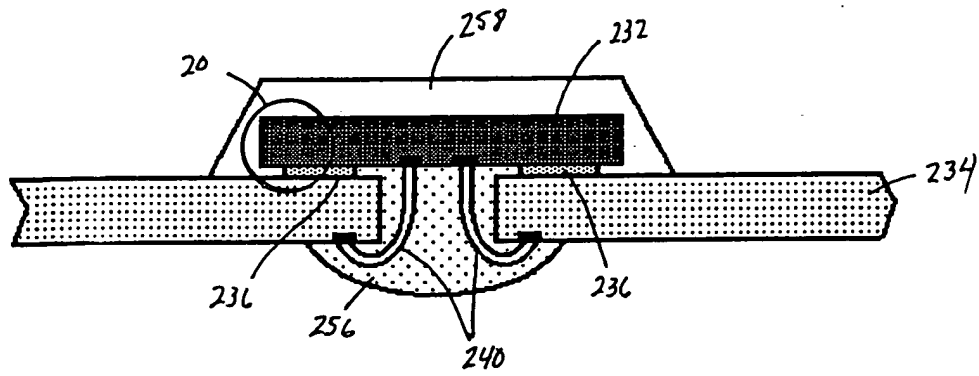
2025-01-01 to 2025-01-01



**FIG. 17**  
PRIOR ART

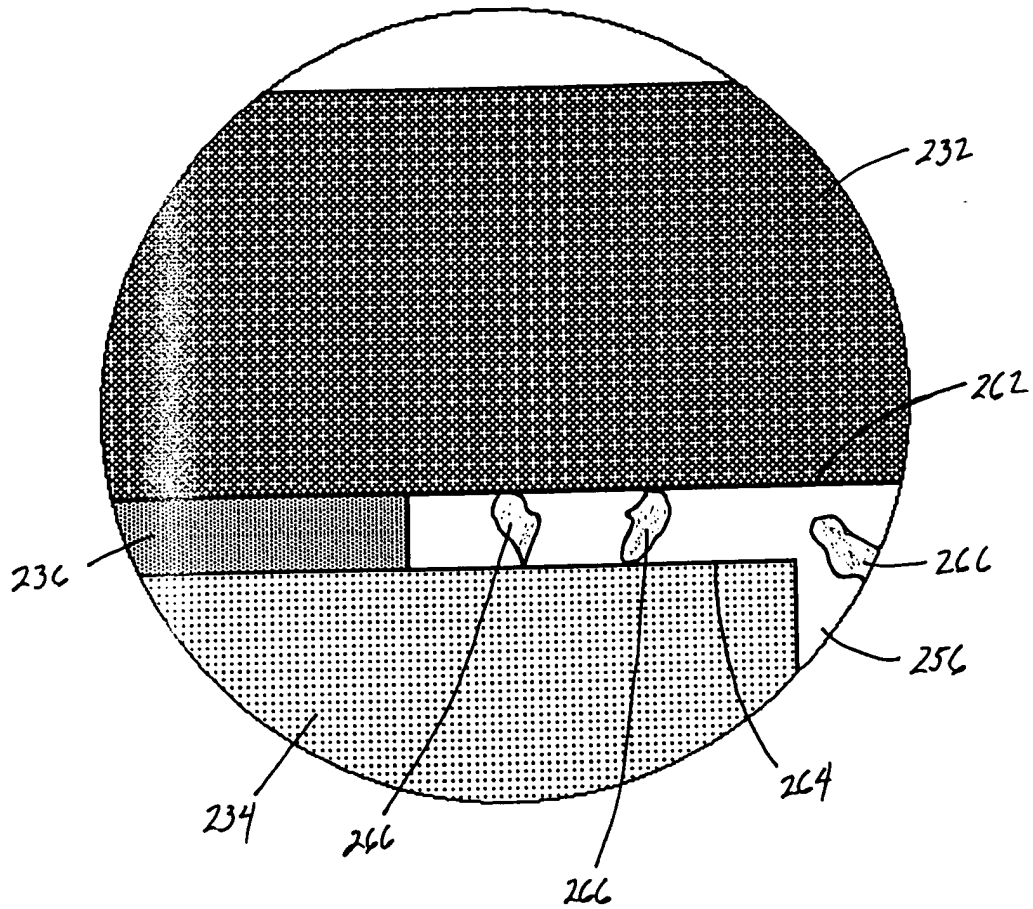


**FIG. 18**  
PRIOR ART



005070" 4E0E+560

**FIG. 19**  
PRIOR ART



**FIG. 20**  
PRIOR ART

